



## **IRF2907ZPBF Information**

Part Number IRF2907ZPBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 75V 75A TO-220AB

TO-220-3 **Package** 

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com

E-mail: salesdept@heisener.com



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# **Certified Quality**

For Reference Only

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









## **IRF2907ZPBF Specifications**

Manufacturer Part NumberIRF2907ZPBFManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsPackageTO-220-3SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°C160A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs270nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7500pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)300W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220AB		
Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-220-3           Series         HEXFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         75V           Current - Continuous Drain (Id) @ 25°C         160A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         270nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         7500pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         300W (Tc)           Rds On (Max) @ Id, Vgs         4.5 mOhm @ 75A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB	Manufacturer Part Number	IRF2907ZPBF
PackageTo-220-3SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°C160A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs270nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7500pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)300W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220AB	Manufacturer	Infineon Technologies
Package         TO-220-3           Series         HEXFET?           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         75 V           Current - Continuous Drain (Id) @ 25°C         160A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         10V           Vgs(th) (Max) @ Id         4V @ 250μA           Gate Charge (Qg) (Max) @ Vgs         270nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         7500pF @ 25V           Vgs (Max)         ±20V           FET Feature         -           Power Dissipation (Max)         300W (Tc)           Rds On (Max) @ Id, Vgs         4.5 mOhm @ 75A, 10V           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-220AB	Category	Discrete Semiconductor Products
SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°C160A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs270nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7500pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)300W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220AB		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75 VCurrent - Continuous Drain (Id) @ 25°C160A (Tc)Drive Voltage (Max Rds On, Min Rds On)10 VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs270nC @ 10 VInput Capacitance (Ciss) (Max) @ Vds7500pF @ 25 VVgs (Max)±20 VFET Feature-Power Dissipation (Max)300W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10 VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220AB	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)75VCurrent - Continuous Drain (Id) @ 25°C160A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id4V @ 250μAGate Charge (Qg) (Max) @ Vgs270nC @ 10VInput Capacitance (Ciss) (Max) @ Vds7500pF @ 25VVgs (Max)±20VFET Feature-Power Dissipation (Max)300W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220AB	Series	HEXFET?
Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  160A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  1750PF @ 25V  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  300W (Tc)  Rds On (Max) @ Id, Vgs  4.5 mOhm @ 75A, 10V  Operating Temperature  Supplier Device Package  75V  160A (Tc)  160A	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  **ET Feature**  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  4.5 mOhm @ 75A, 10V  Operating Temperature  Supplier Device Package  160A (Tc)  160A	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) $Vgs(th)$ (Max) @ Id $4V$ @ $250\mu A$ Gate Charge (Qg) (Max) @ Vgs $270nC$ @ $10V$ Input Capacitance (Ciss) (Max) @ Vds $7500pF$ @ $25V$ $Vgs$ (Max) $\pm 20V$ FET Feature  -  Power Dissipation (Max) $80W$ (Tc)  Rds On (Max) @ Id, Vgs $4.5$ mOhm @ $75A$ , $10V$ Operating Temperature $-55^{\circ}C \sim 175^{\circ}C$ (TJ)  Mounting Type  Through Hole  Supplier Device Package $10V$	Drain to Source Voltage (Vdss)	75V
Vgs(th) (Max) @ Id       4V @ 250μA         Gate Charge (Qg) (Max) @ Vgs       270nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       7500pF @ 25V         Vgs (Max)       ±20V         FET Feature       -         Power Dissipation (Max)       300W (Tc)         Rds On (Max) @ Id, Vgs       4.5 mOhm @ 75A, 10V         Operating Temperature       -55°C ~ 175°C (TJ)         Mounting Type       Through Hole         Supplier Device Package       TO-220AB	Current - Continuous Drain (Id) @ 25°C	160A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  7500pF @ 25V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  4.5 mOhm @ 75A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220AB	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds  7500pF @ 25V  Vgs (Max)  ±20V  FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  4.5 mOhm @ 75A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220AB	Vgs(th) (Max) @ Id	4V @ 250μA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)300W (Tc)Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220AB	Gate Charge (Qg) (Max) @ Vgs	270nC @ 10V
FET Feature -  Power Dissipation (Max) 300W (Tc)  Rds On (Max) @ Id, Vgs 4.5 mOhm @ 75A, 10V  Operating Temperature -55°C ~ 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220AB	Input Capacitance (Ciss) (Max) @ Vds	7500pF @ 25V
Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  4.5 mOhm @ 75A, 10V  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-220AB	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs4.5 mOhm @ 75A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220AB	FET Feature	-
Operating Temperature -55°C ~ 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-220AB	Power Dissipation (Max)	300W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB	Rds On (Max) @ Id, Vgs	4.5 mOhm @ 75A, 10V
Supplier Device Package TO-220AB	Operating Temperature	-55°C ~ 175°C (TJ)
	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Package / Case TO-220-3	Package / Case	TO-220-3
Report errors?		Report errors?

#### **IRF2907ZPBF Guarantees**



### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **IRF2907ZPBF Payment Methods**





















### **IRF2907ZPBF Shipping Methods**













If you have any question about IRF2907ZPBF, please do not hesitate to contact us!

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